Two-dimensional non-volatile programmable pâ€“n jun

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Citation Report

#	Article	IF	Citations
1	Floating-Gate Manipulated Graphene-Black Phosphorus Heterojunction for Nonvolatile Ambipolar Schottky Junction Memories, Memory Inverter Circuits, and Logic Rectifiers. Nano Letters, 2017, 17, 6353-6359.	4.5	87
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